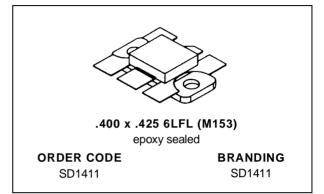
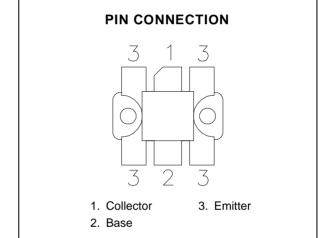


SD1411

RF & MICROWAVE TRANSISTORS HF SSB APPLICATIONS

- 30 MHz
- 40 VOLTS
- IMD -30 dB
- **COMMON EMITTER**
- GOLD METALLIZATION
- P_{OUT} = 200 W MIN. WITH 16 dB GAIN





DESCRIPTION

The SD1411 is a silicon NPN transistor designed for telecommunications in HF and VHF frequency bands. This device utilizes gold metallized die with diffused emitter resistors to achieve high reliability and ruggedness.

ABSOLUTE MAXIMUM RATINGS $(T_{case} = 25^{\circ}C)$

Symbol	Parameter	Value	Unit	
VcBo	Collector-Base Voltage	110	V	
Vceo	Collector-Emitter Voltage	55	V	
V_{EBO}	Emitter-Base Voltage 4.0		V	
Ic	Device Current	40	Α	
P _{DISS}	Power Dissipation	330	W	
TJ	Junction Temperature	+200	°C	
T _{STG}	Storage Temperature	- 65 to +150	°C	

THERMAL DATA

R _{TH(j-c)} Junction-Case Thermal Resistance	0.36	°C/W
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October 1992 1/3

SD1411

ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

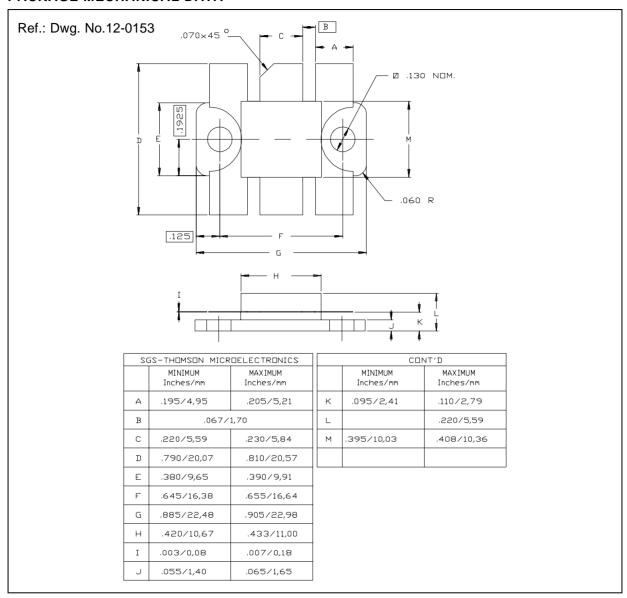
STATIC

Symbol	Test Conditions	Value			Unit		
		Min.	Тур.	Max.	Oilit		
ВУсво	I _C = 200mA	$I_E = 0mA$		110		_	V
BVces	I _C = 200mA	$V_{BE} = 0V$		110	_	_	V
BV _{CER}	I _C = 200mA	$R_{BE} = 10\Omega$		100	_	_	V
BV _{CEO}	I _C = 200mA	$I_B = 0mA$		55	_	_	V
BV _{EBO}	I _E = 20mA	$I_C = 0mA$		4.0	_	_	V
I _{CES}	V _{CE} = 45V	I _E = 0mA			_	20	mA
hFE	Vce = 6V	I _C = 10A		15	_	80	_

DYNAMIC

Symbol	Test Conditions		Value			Unit	
Symbol	rest Conditions			Min.	Тур.	Max.	Oiiit
Pout	f = 30 MHz	$V_{CE} = 40 V$	$I_{CQ} = 150 \text{ mA}$	200	_	_	W
G _P	f = 30 MHz	$V_{CE} = 40 V$	$I_{CQ} = 150 \text{ mA}$	16	_	_	dB
IMD	f = 30 MHz	V _{CE} = 40 V	I _{CQ} = 150 mA	_	_	-30	dB
Сов	f = 1 MHz	$V_{CB} = 50 \text{ V}$		_	_	360	pF

PACKAGE MECHANICAL DATA



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